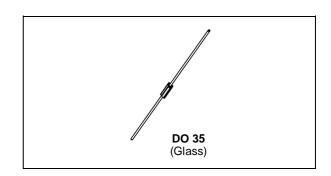


SMALL SIGNAL SCHOTTKY DIODE

DESCRIPTION

Metal to silicon junction diode featuring high breakdown, low turn-on voltage and ultrafast switching. Primarly intended for high level UHF/VHF detection and pulse application with broad dynamic range. Matched batches are available on request.



ABSOLUTE RATINGS (limiting values)

Symbol	Parameter	Value	Unit	
V_{RRM}	Repetitive Peak Reverse Voltage		70	V
l _F	Forward Continuous Current*	15	mA	
P _{tot}	Power Dissipation*	430	mW	
T _{stg} T _j	Storage and Junction Temperature Range	- 65 to 200 - 65 to 200	°C	
TL	Maximum Lead Temperature for Soldering during from Case	230	°C	

THERMAL RESISTANCE

	Symbol	Test Conditions	Value	Unit
Ī	R _{th(j-a)}	Junction-ambient*	400	°C/W

ELECTRICAL CHARACTERISTICS

STATIC CHARACTERISTICS

Symbol		Min.	Тур.	Max.	Unit		
V_{BR}	$T_{amb} = 25^{\circ}C$	$I_R = 10\mu A$		70			٧
V _F * *	T _{amb} = 25°C	$I_F = 1 \text{mA}$				0.41	٧
	T _{amb} = 25°C	$I_F = 15mA$				1	
I _R * *	T _{amb} = 25°C	$V_R = 50V$				0.2	μΑ

DYNAMIC CHARACTERISTICS

Symbol	Test Conditions				Тур.	Max.	Unit
С	T _{amb} = 25°C	$V_R = 0V$	f = 1MHz			2	рF
τ	T _{amb} = 25°C	$I_F = 5mA$	Krakauer Method			100	ps

^{*} On infinite heatsink with 4mm lead length ** Pulse test: $t_p \le 300 \mu s$ $\delta < 2\%$.

Matched batches available on request. Test conditions (forward voltage and/or capacitance) according to customer specification.

November 1994 1/3

Figure 1. Forward current versus forward voltage at low level (typical values).

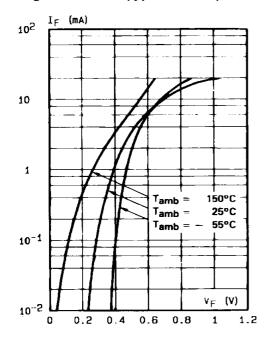


Figure 2. Capacitance C versus reverse applied voltage $V_{\rm R}$ (typical values).

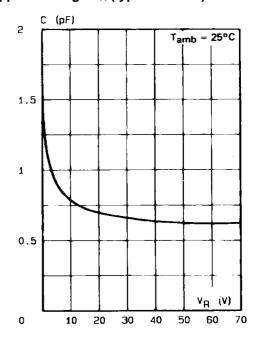


Figure 3. Reverse current versus ambient temperature.

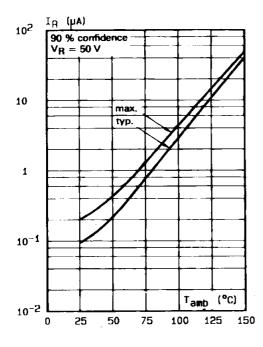
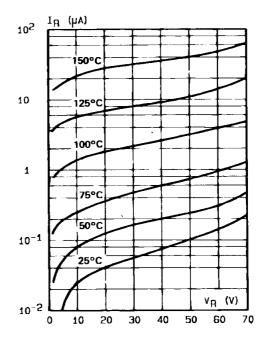
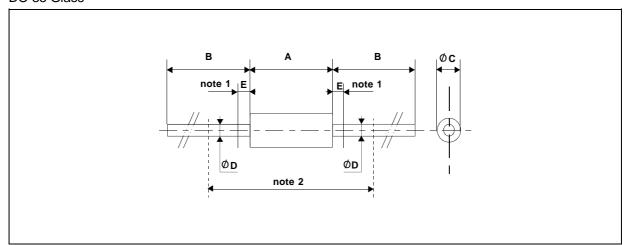


Figure 4. Reverse current versus continuous reverse voltage (typical values).



PACKAGE MECHANICAL DATA

DO 35 Glass



	DIMENSIONS						
REF.	F. Millimeters		Inches		NOTES		
	Min.	Max.	Min.	Max.			
Α	3.050	4.500	0.120	0.117	1 - The lead diameter Ø D is not controlled over zone E		
В	12.7		0.500				
ØC	1.530	2.000	0.060	0.079	2 - The minimum axial lengh within which the device may be placed with its leads bent at right angles is 0.59"(15 mm)		
ØD	0.458	0.558	0.018	0.022	placed with its leads bent at right angles is 0.59 (15 min)		
Е		1.27		0.050			

Cooling method : by convection and conduction Marking: clear, ring at cathode end. Weight: 0.15g

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